FAIRCHILD SEMICONDUCTOR TM

November 1998

FDR8308P

Dual P-Channel, Logic Level, PowerTrench™ MOSFET

General Description

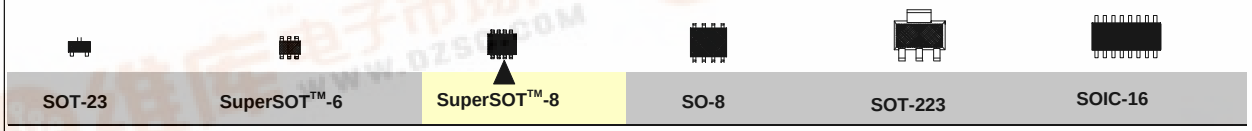
The SuperSOT-8 family of P-Channel Logic Level MOSFETs have been designed to provide a low profile, small footprint alternative to industry standard SO-8 little foot type product.

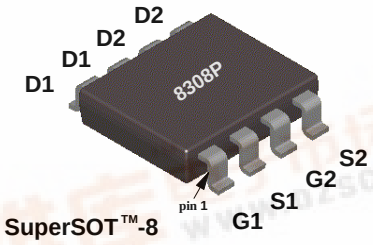
These P-Channel Logic Level MOSFETs are produced using Fairchild Semiconductor's advanced PowerTrench process that has been tailored to minimize the on-state resistance and yet maintain superior switching performance.

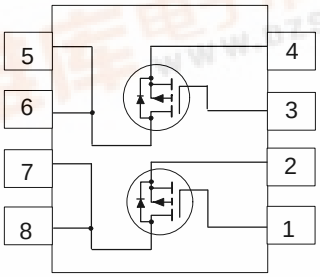
These devices are well suited for portable electronics applications: load switching and power management, battery charging circuits, and DC/DC conversion.

Features

- -3.2 A, -20 V. $R_{DS(ON)}$ = 0.050 Ω @ V_{GS} = -4.5 V,
  $R_{DS(ON)}$ = 0.070 Ω @ V_{GS} = -2.5 V.
- Low gate charge (13nC typical).
- High performance trench technology for extremely low $R_{DS(ON)}$.
- SuperSOT™-8 package: small footprint (40% less than SO-8); low profile(1mmthick); maximum power comparable to SO-8.







Absolute Maximum Ratings T_A = 25°C unless otherwise noted

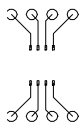
Symbol	Parameter	FDR8308P	Units
V_{DSS}	Drain-Source Voltage	-20	V
V_{GSS}	Gate-Source Voltage	±8	V
I_D	Draint Current - Continuous (Note 1)	-3.2	A
	- Pulsed	-20	
P_D	Maximum Power Dissipation (Note 1)	0.8	W
T_J,T_{STG}	Operating and Storage Temperature Range	-55 to 150	°C
THERMAL CHARACTERISTICS			
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1)	156	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	40	°C/W

Electrical Characteristics (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = -250 µA	-20			V
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	I_D = -50 µA, Referenced to 25 °C		-16		mV /°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = -16 V, V_{GS} = 0 V			-1	µA
		T_J = 55°C			-10	µA
I_{GSS}	Gate - Body Leakage Current	V_{GS} = 8 V, V_{DS} = 0 V			100	nA
I_{GSS}	Gate - Body Leakage, Reverse	V_{GS} = -8 V, V_{DS} = 0 V			-100	nA
ON CHARACTERISTICS (Note 2)						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = -250 µA	-0.4	-0.9	-1.5	V
$\Delta V_{GS(th)}/\Delta T_J$	Gate Threshold Voltage Temp.Coefficient	I_D = -50 µA, Referenced to 25 °C		2.5		mV /°C
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS} = -4.5 V, I_D = -3.2 A		0.038	0.05	Ω
		T_J = 125°C		0.053	0.075	
		V_{GS} = -2.5 V, I_D = -2.7 A		0.054	0.07	
$I_{D(ON)}$	On-State Drain Current	V_{GS} = -4.5 V, V_{DS} = -5 V	-20			A
g_{FS}	Forward Transconductance	V_{DS} = -4.5 V, I_D = -3.2 A		13		S
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	V_{DS} = -10 V, V_{GS} = 0 V, f = 1.0 MHz		1240		pF
C_{oss}	Output Capacitance			270		pF
C_{rss}	Reverse Transfer Capacitance			100		pF
SWITCHING CHARACTERISTICS (Note 2)						
$t_{D(on)}$	Turn - On Delay Time	V_{DD} = -5 V, I_D = -1 A,		8	16	ns
t_r	Turn - On Rise Time	V_{GS} = -4.5 V, R_{GEN} = 6 Ω		15	27	ns
$t_{D(off)}$	Turn - Off Delay Time			45	65	ns
t_f	Turn - Off Fall Time			30	50	ns
Q_g	Total Gate Charge	V_{DS} = -10 V, I_D = -4.5 A,		13	19	nC
Q_{gs}	Gate-Source Charge	V_{GS} = -4.5 V		1.8		nC
Q_{gd}	Gate-Drain Charge			3		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
I_S	Maximum Continuous Drain-Source Diode Forward Current				-0.67	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0 V, I_S = -0.67 A (Note 2)		-0.7	-1.2	V

Notes:

1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



156°C/W on a 0.0025 in^2 pad of 2oz copper.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2.0%.

Typical Electrical Characteristics

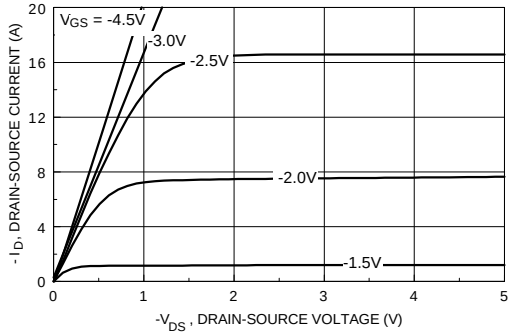


Figure 1. On-Region Characteristics.

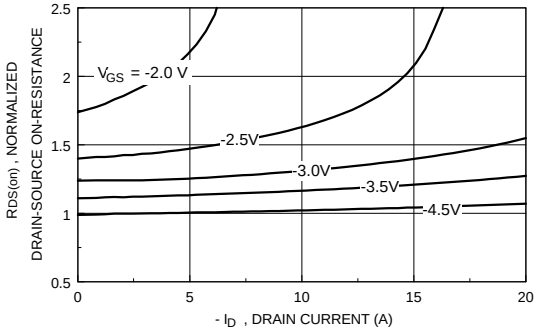


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

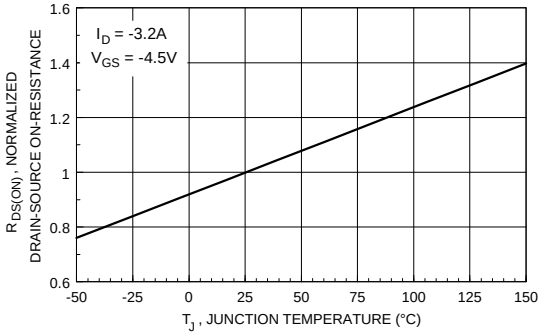


Figure 3. On-Resistance Variation with Temperature.

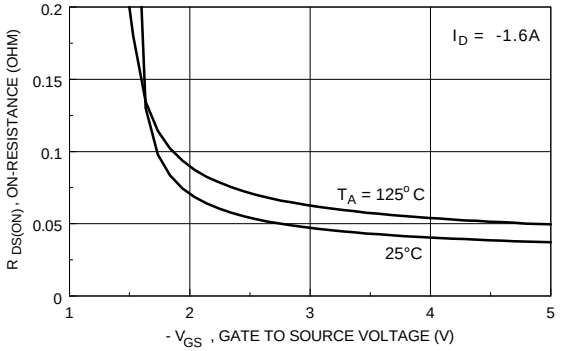


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

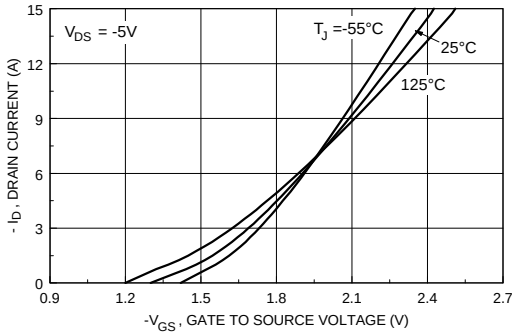


Figure 5. Transfer Characteristics.

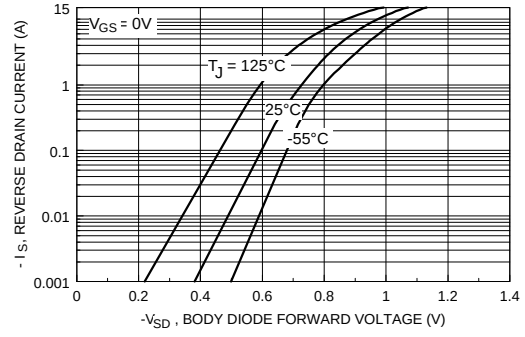


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Electrical Characteristics (continued)

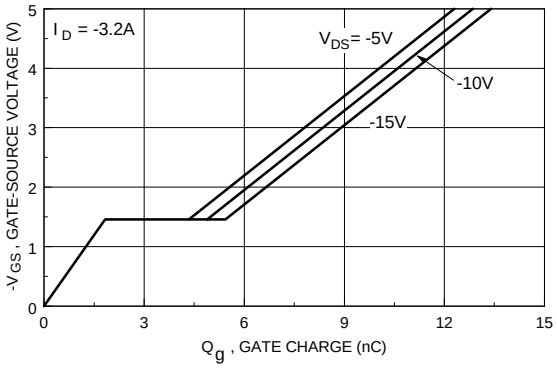


Figure 7. Gate Charge Characteristics.

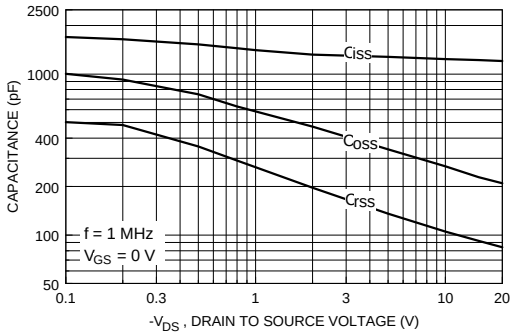


Figure 8. Capacitance Characteristics.

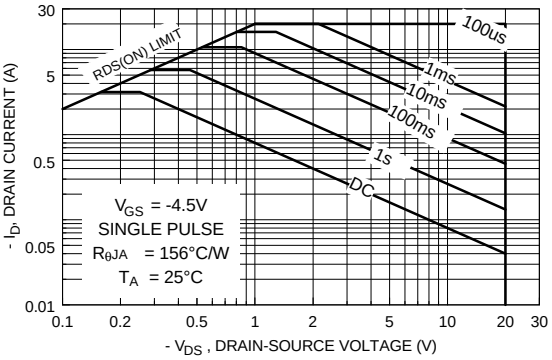


Figure 9. Maximum Safe Operating Area.

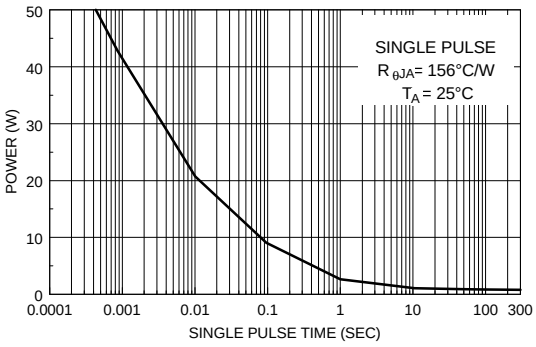


Figure 10. Single Pulse Maximum Power Dissipation.

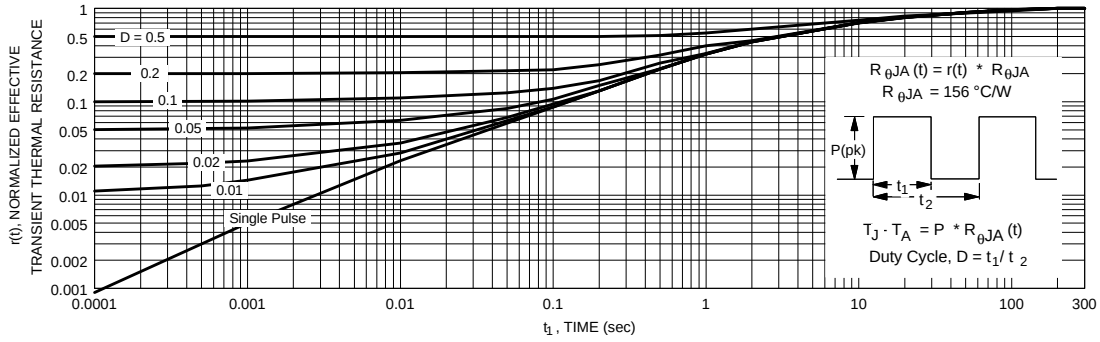


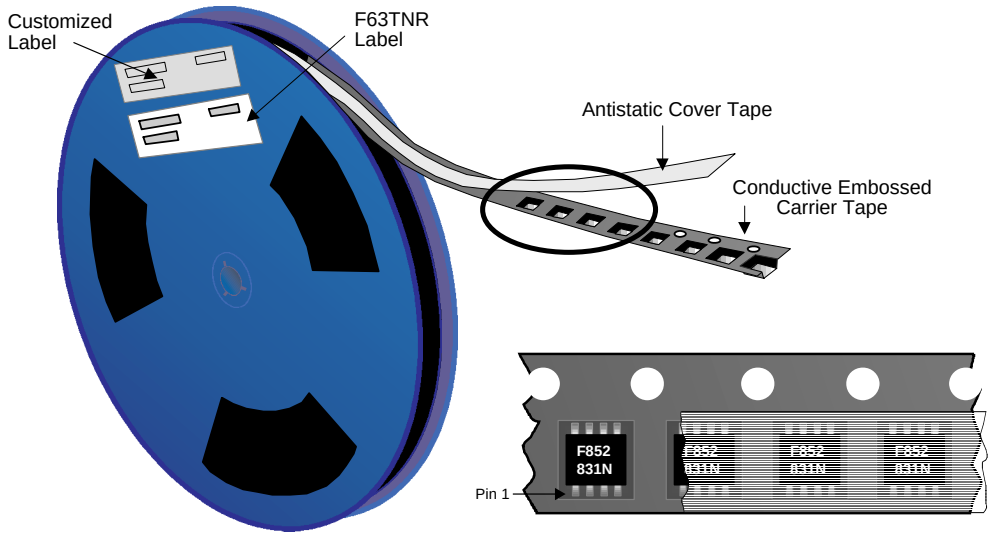
Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in note 1.

Transient thermal response will change depending on the circuit board design.

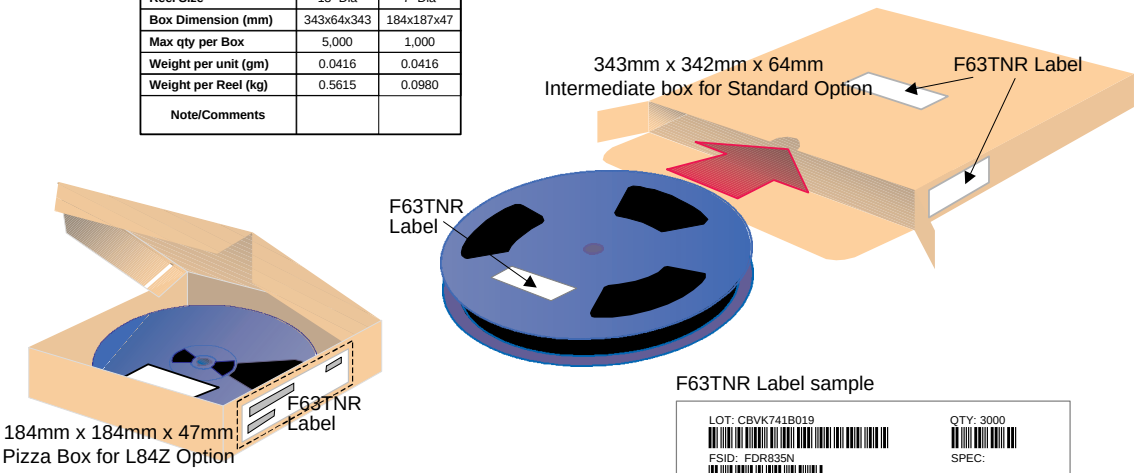
SuperSOT™-8 Tape and Reel Data and Package Dimensions

SSOT-8 Packaging
Configuration: Figure 1.0



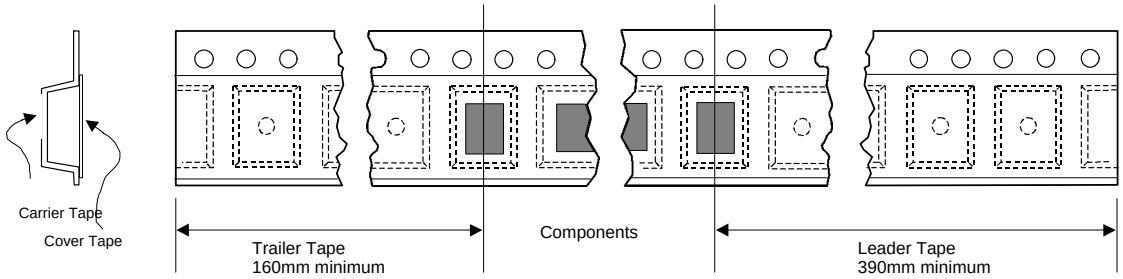
SSOT-8 Unit Orientation

SSOT-8 Packaging Information		
Packaging Option	Standard (no flow code)	L84Z
Packaging type	TNR	TNR
Qty per Reel/Tube/Bag	3,000	500
Reel Size	13" Dia	7" Dia
Box Dimension (mm)	343x64x343	184x187x47
Max qty per Box	5,000	1,000
Weight per unit (gm)	0.0416	0.0416
Weight per Reel (kg)	0.5615	0.0980
Note/Comments		



F63TNR Label sample

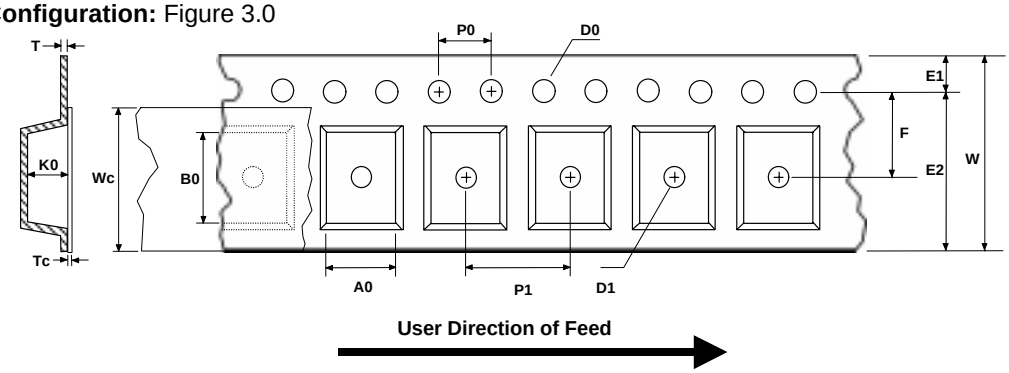
SSOT-8 Tape Leader and Trailer
Configuration: Figure 2.0



SuperSOT™-8 Tape and Reel Data and Package Dimensions, continued

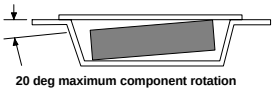
SSOT-8 Embossed Carrier Tape

Configuration: Figure 3.0

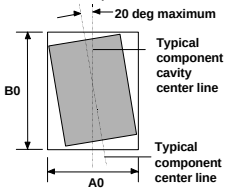


Dimensions are in millimeter														
Pkg type	**A0**	**B0**	**W**	**D0**	**D1**	**E1**	**E2**	**F**	**P1**	**P0**	**K0**	**T**	**Wc**	**Tc**
SSOT-8 (12mm)	4.47 +/-0.10	5.00 +/-0.10	12.0 +/-0.3	1.55 +/-0.05	1.50 +/-0.10	1.75 +/-0.10	10.25 min	5.50 +/-0.05	8.0 +/-0.1	4.0 +/-0.1	1.37 +/-0.10	0.280 +/-0.150	9.5 +/-0.025	0.06 +/-0.02

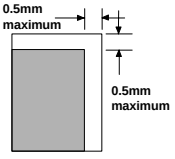
Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

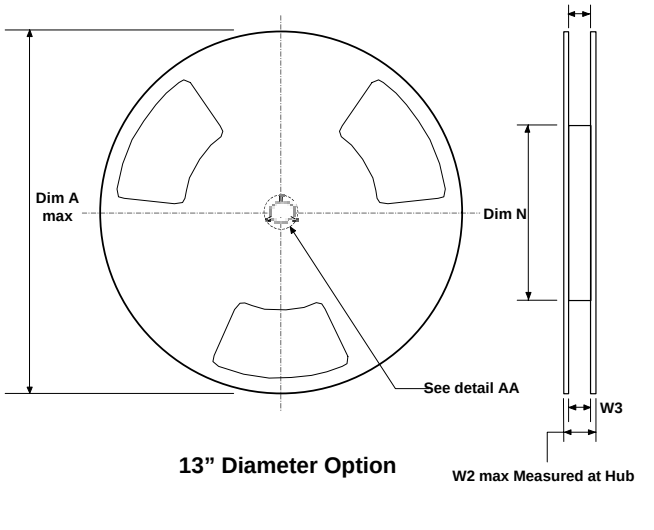


Sketch B (Top View)
Component Rotation

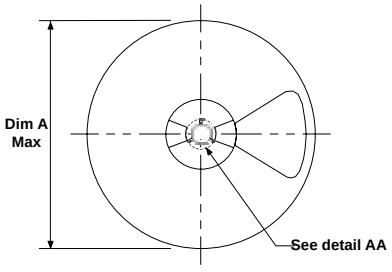


Sketch C (Top View)
Component lateral movement

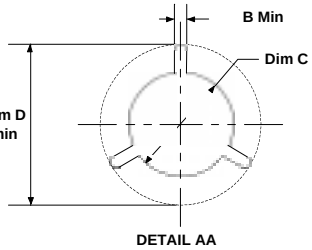
SSOT-8 Reel Configuration: Figure 4.0



13" Diameter Option



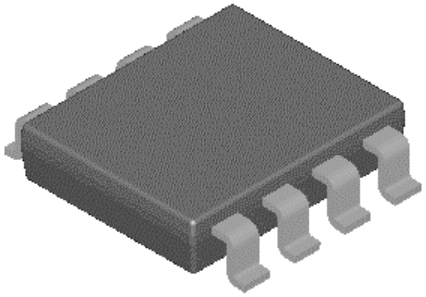
7" **Diameter Option**

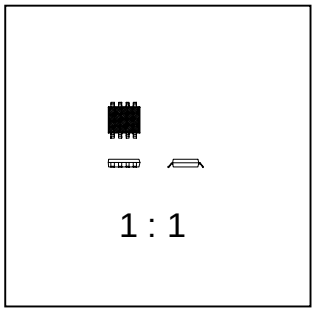


Dimensions are in inches and millimeters									
Tape Size	**Reel Option**	**Dim A**	**Dim B**	**Dim C**	**Dim D**	**Dim N**	**Dim W1**	**Dim W2**	**Dim W3 (LSL-USL)**
12mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	5.906 150	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 – 0.606 11.9 – 15.4
12mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	7.00 178	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 – 0.606 11.9 – 15.4

SuperSOT™-8 Tape and Reel Data and Package Dimensions, continued

SuperSOT™-8 (FS PKG Code 34, 35)

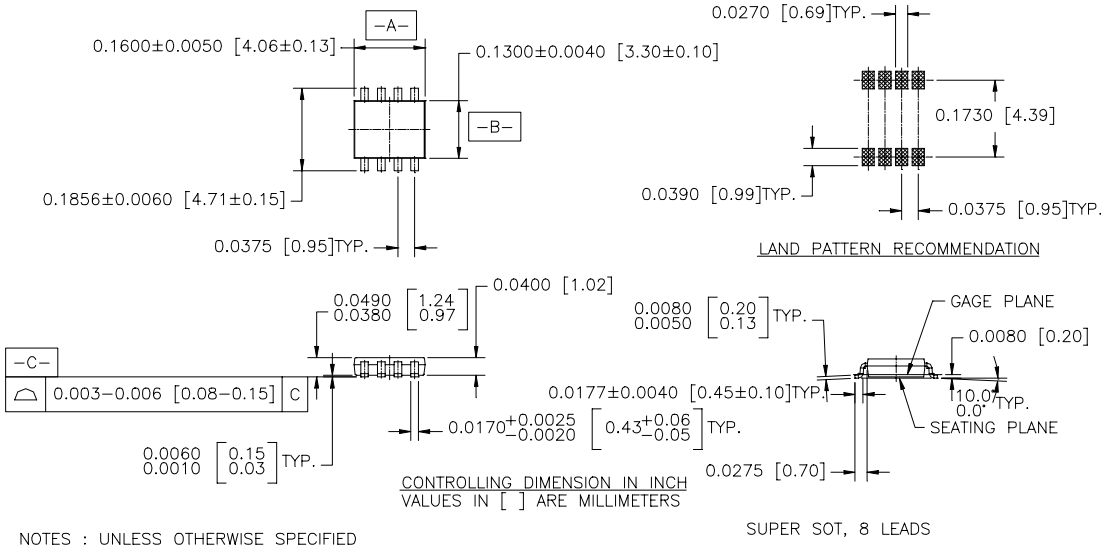




Scale 1:1 on letter size paper

Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.0416



NOTES : UNLESS OTHERWISE SPECIFIED

1. STANDARD LEAD FINISH TI BE 200 MICROINCHES / 5.08 MICROMETERS MINIMUM TIN/LEAD (SOLDER) ON COPPER.
2. NO JEDEC REGISTRATION AS JAN. 1996

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SuperSOT™-3
SuperSOT™-6
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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.